

## IN THE CLAIMS

Claims 1-7 (Canceled).

8 (Currently Amended). A method comprising:  
increasing the viscosity of a wet etchant by dehydrating the etchant to reduce the amount of undercutting of an etched layer.

Claim 9 (Canceled).

10 (Original). The method of claim 8 including increasing the viscosity of the etchant by adding a thickening agent to said etchant.

11 (Original). The method of claim 8 including applying said increased viscosity wet etchant to a semiconductor wafer to etch a layer on said wafer.

12 (Currently Amended). A wet etchant comprising:  
a material including sulfuric acid to etch a semiconductor layer; and  
a thickening agent.

13 (Original). The etchant of claim 12 wherein said thickening agent is glycol.

14 (Original). The etchant of claim 12 wherein said thickening agent is glycerol.

Claim 15 (Canceled).

16 (Original). A wet etchant comprising:  
a dehydrated etching material.

17 (Original). The etchant of claim 16 wherein said material is sulfuric acid.

18 (Currently Amended). A wet etchant comprising:  
a material including sulfuric acid to etch a semiconductor layer, said material having a viscosity of greater than one centipoise.

19 (Original). The etchant of claim 18 wherein said etchant is dehydrated.

20 (Original). The etchant of claim 18 including a thickening agent.

21 (Original). The etchant of claim 18 including sulfuric acid.